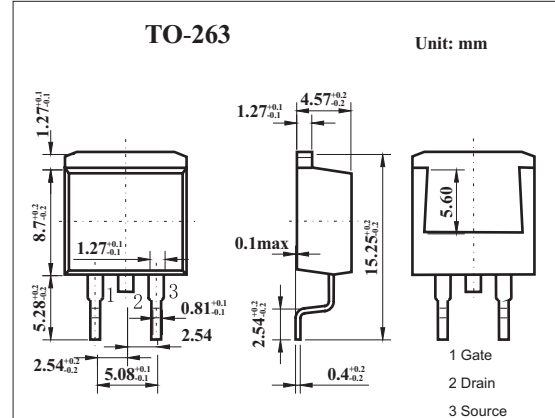


N-Channel Enhancement Mode MOSFET 2SK3494

■ Features

- Low on-resistance, low Qg
- High avalanche resistance



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	20	A
	I _{DP} *	80	A
Power dissipation	P _D	T _C =25°C	50
		T _A =25°C	1.4
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs, Duty Cycle ≤ 1%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Drain cut-off current	I _{DSS}	V _{DS} =200V, V _{GS} =0			10	μA	
Gate leakage current	I _{GSS}	V _{GS} =±30V, V _{DS} =0			±1	μA	
Gate threshold voltage	V _{th}	V _{DS} =10V, I _D =1mA	2.0		4.0	V	
Forward transfer admittance	Y _{fs}	V _{DS} =10V, I _D =10A	7	14		S	
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A		82	105	mΩ	
Input capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0, f=1MHZ		2450		pF	
Output capacitance	C _{oss}				356		pF
Reverse transfer capacitance	C _{rss}				40		pF
Turn-on delay time	t _{on}	I _D =10A, V _{GS(on)} =10V, R _L =10Ω, V _{DD} =100V		36		ns	
Rise time	t _r			20		ns	
Turn-off delay time	t _{off}			184		ns	
Fall time	t _f			29		ns	
Total Gate Charge	Q _G	I _D =10A, V _{DD} =100V, V _{GS} =10V		41		nC	
Gate to Source Charge	Q _{GS}			8.4		nC	
Gate to Drain Charge	Q _{GD}			14		nC	